Coulomb blockade and non-Ferm i-liquid behavior in quantum dots

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The non-Fem i-liquid properties of an ultrasm all quantum dot coupled to a lead and to a quantum box are investigated. Tuning the ratio of the tunneling am plitudes to the lead and box, we nd a line of two-channel K ondo xed points for arbitrary C oulom b repulsion on the dot, governing the transition between two distinct Fem i-liquid regimes. The Fem i liquids are characterized by di erent values of the conductance. For an asymmetric dot, spin and charge degrees of freedom are entangled: a continuous transition from a spin to a charge two-channel K ondo e ect evolves. The crossover tem perature to the two-channel K ondo e ect is greatly enhanced away from the localm om ent regime, making this exotic e ect accessible in realistic quantum -dot devices.

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Strongly correlated electron systems display non-Ferm i-liquid properties in the vicinity of a zerotem perature phase transition.^{1,2} In lattice system s, the nature of these so-called quantum critical points is still not well understood. W hile theoretical descriptions typically start from well-de ned quasiparticle excitation modes, the non-Ferm i-liquid behavior is interaction driven, and arises from persisting quantum -m echanical uctuations between these modes.^{1,2} The two-channel K ondo e ect (2CKE) is a prototype for such a quantum critical point in a quantum impurity system. It occurs when a spin $\frac{1}{2}$ localm on ent is coupled antiferrom agnetically with equal strength to two independent conductionelectron channels that overscreen the moment.³ Its xed point governs the transition between two distinct Ferm i liquids, which are adiabatically connected at nite tem perature. W hile certain ballistic m etallic point contacts, two-level systems, and heavy ferm ion alloys have been argued to display the 2CKE, 3 a conclusive experimental observation of this elusive e ect remains lacking.

Quantum -dot devices have become an important tool for investigating fundamental questions such as the 2CKE, since they allow for detailed sample engineering and direct control of the m icroscopic m odel param eters. Here we investigate realizations of the 2CKE in a doubledot device, com prised of a quantum box (i.e., a large dot) indirectly coupled to a lead via an ultrasm all quantum dot.⁴ In the Coulom b-blockade valleys, charge uctuations are suppressed on the quantum box. This blocks the interlead exchange coupling at tem peratures below the charging energy of the box, thereby generating two independent screening channels for the localm om ent form ed on the sm alldot.⁵ A spin 2CKE then develops on the dot if the e ective spin-exchange couplings to the lead and box are tuned to be equal.⁵ So far, only the local-m om ent regime was considered within this scenario.^{5,6,7}

In this paper, we explore di erent regim es of the lead { dot{box device, where charge is not quantized on the quantum dots. We nd the following: (i) a line of twochannel xed points as a function of the gate voltages in the device, extending to the mixed-valent regim e of the ultrasm all dot and away from the C oulom b-blockade valleys of the quantum box; (ii) a continuous transition from a spin 2CKE to a charge 2CKE for an asymmetric dot; (iii) an intriguing entanglement of spin and charge within the 2CKE that develops in the experimentally relevant case of particle-hole asymmetry, rejected in a simultaneous h(T) divergence of the magnetic susceptibility of the dot and the charge capacitance of the box; (iv) an abrupt jump in the T = 0 conductance across the two-channel line. Here the Fermi i liquids on either side of the critical line are characterized by distinct values of the T = 0 conductance.

The setting we consider consists of an ultrasm all quantum dot, modeled by a single energy level $_d$ and an onsite repulsion U, embedded between a metallic lead and a quantum box. The quantum box is characterized by a nite charging energy, E $_c$, and by a dense set of single-particle levels, which we take to be continuous. Denoting the creation of an electron with spin projection on the dot by d^y, the corresponding H am iltonian reads

$$H = \begin{bmatrix} X & X \\ & & \\ &$$

where $C_{L\,k}^{y}$ ($C_{B\,k}^{y}$) creates a lead (box) electron with momentum k and spin projection , t_{L} (t_{B}) is the tunneling matrix element between the quantum dot and the lead (box), $_{L\,k}$ ($_{B\,k}$) are the single-particle levels in the lead (box), and \hat{n}_{d} equals $d^{y}d_{p}$. The excess number of electrons inside the box, $\hat{n}_{B} = {}_{k} [C_{B\,k}^{y} C_{B\,k} (B_{K})]$, is controlled by the dimensionless gate voltage, N_{B} .

We treat the Ham iltonian of Eq. (1) using a recent adaptation of W ilson's num erical renorm alization-group (NRG) method⁸ to the C oulomb blockade.⁹ Introducing three collective charge operators for the box,¹⁰ $\hat{N} = \frac{1}{m=-1}$ m jn ilm j and $\hat{N} = \frac{1}{m=-1}$ jn lilm j we replace the tunneling term petween the dot and the box in Eq. (1) with $_{k}^{P}$ t_B \hat{N}^{+} c_B^V d + H c: , while the charging-energy term is converted to E_c ($\hat{N} = N_{B}$)².



FIG. 1: The magnetic susceptibility of the dot vs T, for $_{L} = E_{C} = 0.1D$, N $_{B} = 0$, and di erent values of U = 2_{d} . Here $_{B}$ is tuned for each value of U to the two-channel point $_{D}^{2CK}$. The K ondo temperature T_K is de ned in Eq. (2). For all U, ranging from the local-moment regime U $_{L}$, to the strongly mixed-valent regime U = 0, to negative U (not shown), there exists a two-channel point $_{D}^{2CK}$ where (T) diverges logarithm ically as T ! 0, and the nite-size spectrum converges to the conventional two-channel xed point. Inset: T_K vsU. For U $_{L}$; E_C (local-moment regime), T_K decreases exponentially with U. For U < $_{L}$ (mixed-valent regime), it exceeds E c.

Since the dynam ics of \hat{N} is insensitive to the precise num – ber of conduction electrons in the bands, one can relax the constraint $\hat{N} = \hat{n}_B$, and regard \hat{N} as an independent degree of freedom .⁹ The resulting H am iltonian describes then two noninteracting conduction bands coupled to a complex in purity, composed of both \hat{N} and the dot degrees of freedom . Taking the two conduction baths to have a common rectangular density of states, () = (D j), we solve the resulting model using the NRG . Here the number N_s of NRG states retained sets a low er bound on the ratio $E_C = D$ one can treat. Throughout the paper we set the NRG discretization param eter⁸

equal to 2:8, while N $_{\rm s}$ = 2000.

We begin with a symmetric dot, U = $2_{\rm d}$, and with a box tuned to the middle of a Coulom b-blockade valley, $N_{\rm B} = 0$. Fixing E_C and the hybridization strength to the lead, $L = \frac{t_{\rm L}^2}{t_{\rm L}^2}$, we varied the hybridization to the $t_{\rm B}^2$, in search of a 2CKE.Our results for $box_{,B} =$ $E_{C} = L = 0:1D$ are sum marized in Fig. 1. Quite surprisingly, we nd a two-channel K ondo point $\frac{2CK}{B}$ for all values of U, ranging from the local-m om ent regim e IJ $_{\rm L}$, to the strongly m ixed-valent regim e U 0, to the unrealistic regime of U < 0. The development of a 2CKE is relected in a logarithm ic divergence of the dot susceptibility¹¹ as T ! 0 (see Fig. 1), and in a nitesize spectrum that converges to the conventional twochannel xed point (i.e., identical energies, degeneracies, and quantum num bers).

The emergence of a spin 2C K E for U $_{L}$ proves the scenario of Ref. 5. Speci cally, the associated K ondo tem perature decays exponentially with U for U $_{\rm L}$;E $_{\rm C}$ (inset of Fig. 1), while the ratio $_{\rm B}^{\rm 2C\,K}$ = $_{\rm L}$ approaches the asymptotic value 1 + 2E $_{\rm C}$ =U (not shown). Here and throughout the paper we dene the K ondo tem – perature $T_{\rm K}$ according to the Bethe ansatz expression for the slope of the ln (T) diverging term in the susceptibility of the two-channel K ondo m odel, 12

(T)
$$\frac{(B g)^2}{20k_B T_K} \ln (T_K = T)$$
: (2)

W e em phasize, however, that our NRG calculations go well beyond the Schrie er-W ol transform ation used in Ref.5, con m ing that no relevant perturbations are generated at higher orders in the tunneling am plitudes.

Contrary to the local-m om ent regim e, the developm ent of a spin 2CKE in the mixed-valent regim e (let alone for U < 0) is an unexpected feature, with no apparent spin degree of freedom to be overscreened. Moreover, $T_{\rm K}$ is signi cantly enhanced for U -0, exceeding $E_{\rm C}$ in Fig. 1. This behavior is rem iniscent of the two-channel Anderson model, where the 2CKE likewise persists into the mixed-valent regim e. 13 Particularly intriguing is the limit of a noninteracting dot, which reduces 4 to the familiar problem of a quantum box connected to a lead by single-mode tunneling. A lihough a charge 2CKE was predicted for the latter setting at the degeneracy points of the C oulom b blockade, 14 no spin 2CKE was previously anticipated.

To understand the 2CKE for U = 0, we revisit the problem of a quantum box connected to a lead by a nearly fully transm itting single-m ode point contact. Following Refs. 15 and 16, we model this system by a one-dimensional (1D) geometry, where x < 0 (x > 0) represents the lead (box), and x = 0 corresponds to the noninteracting dot. The deviation from perfect transm ission is modeled^{15,16} by weak backscattering at x = 0. Extending the bosonization treatment of Ref. 16 to a nite local magnetic eld acting on the dot, and carefully accounting for an underlying symmetry of the Ham iltonian,¹⁷ we obtain the following linear magnetic susceptibility for $k_B T = E_c$:

$$(T) = {}_{0} \frac{{}_{B} g}{h v_{F}}^{2} \ln \frac{D_{e}}{2 k_{B} T} \frac{1}{2} + \frac{1}{2 k_{B} T} ;$$
(3)

where $_0 = = (4 \text{ R})$ and $= \text{R} (8 \text{ E}_{\text{C}} = {}^2) \cos^2(\text{ N}_{\text{B}})$. Here, R is the relation, v_F is the Fermi velocity, equals e^{C} with C 0.5772, (x) is the digamma function, and D_e is an elective cuto of the order of E_C.

Equation (3) features a logarithm ic tem perature dependence down to $k_B T$. Hence, (T) diverges logarithm ically for perfect transm ission, when / R vanishes. In fact, (T) diverges logarithm ically at perfect transm ission for all gate voltages, except for half-integer values of N_B where $_0$ vanishes. In particular, Eq. (3) predicts T_K (N_B) / $1=\cos^2(N_B)$.

Equation (3) form ally describes the limit E_c $_L$, since $_L$ serves as the elective bandwidth for the 1D model used (see Ref. 4, Sec. III). Surprisingly, we ind



FIG. 2: $1=T_{\rm K}$ vs N_B for U = $_{\rm d}$ = 0 and $_{\rm L}$ =D = 0.1. Here E $_{\rm C}$ =D equals 0.1 (circles) and 0.01 (pluses). For each combined value of N_B and E $_{\rm C}$, the coupling $_{\rm B}$ is tuned to the two-channelpoint $_{\rm B}^{2C\,\rm K}$. As a function of N_B, $_{\rm B}^{2C\,\rm K}$ (N_B) varies by less than 0.2% for each xed value of E $_{\rm C}$. The ratio T_K (0)=T_K (N_B) is well described by cos² (N_B) (solid line). Inset: The box charge hN i vs N_B for $_{\rm L}$ = E $_{\rm C}$ = 0.1D and U = $_{\rm d}$ = 0. Here $_{\rm B}$ = $_{\rm L}$ equals 1 (squares), 1.72 (lled circles + solid line), and 3.24 (crosses). The C oulom b staircase is com pletely washed out for $_{\rm B}$ = $_{\rm E}^{2C\,\rm K}$ (0) = 1.72 $_{\rm L}$, but is gradually recovered upon departure from $_{\rm B}^{2C\,\rm K}$ (0).

good agreem ent with the NRG results for U = 0 even for $E_{\rm C}$ as large as $_{\rm L}$. (i) Scanning N_B for xed $E_{\rm C}$ and $_{\rm L}$, we nd a 2CKE for all gate voltages, with a K ondo tem perature that varies as T_K (N_B) / $1 = \cos^2(N_B)$ (Fig.2). (ii) Consistent with the notion of perfect transmission, only small variations are found in $~_{\rm B}^{\rm 2C\,K}$ (N $_{\rm B}$) as a function of N $_{\rm B}$ (less than 0:2%), falling within our num erical percision. (iii) The Coulomb staircase in the charging of the box is washed out for $_{B} = \frac{2CK}{B}$ (0), but is gradually recovered as $_{\rm B}$ su ciently departs from ^{2C K}_B (0), whether above or below (inset of Fig. 2). (iv) Upon reducing $E_{C} = L$ from 1 to 0:081, the ratio $B_{B}^{2CK}(0) = L$ steadily decreases from 1:72 to 1:11. This suggests the $\lim_{B} \lim_{B} \frac{2CK}{R}$! Las E_{C} ! 0, m atching the condition for perfect transm ission for two noninteracting leads. Thus, the spin 2CKE for U = 0 is well described by Eq. (3).

So farwe have considered a symmetric dot, and varied 2_d. In reality, however, U is large and xed. U = The experim entally tunable param eters are the dot level $_{\rm d}$, the dimensionless gate voltage N $_{\rm B}$, and, to a lesser degree, the tunneling rates $_{\rm L}$ and $_{\rm B}$. In Figs. 3 and 4 we explore the 2CKE as a function d, for U=D = 2 and $L = E_C = 0.1D$. Figure 3(a) shows the two-channel line $B_{\rm B}^{\rm 2CK} = L_{\rm L}$ versus d, for N $_{\rm B}$ = 0. The two-channel line separates two distinct Ferm i liquids, where the dot is coupled more strongly to the box (for $_{\rm B}$ above the line) or to the lead (below and to the side of the line). Deep in the local-m om ent regim e there is good agreem ent with the estim ate of Ref. 5 based on the Schrie er-W ol transform ation (dashed line). How ever, large deviations develop as one approaches the mixed-valent regime.

Fixing $_{\rm B}$ at the N $_{\rm B}$ = 0 value of $_{\rm B}^{\rm 2CK}$, the shape of



FIG.3: (a) The two-channel line $_{\rm B}^{2C\,{\rm K}}$ = $_{\rm L}$ vs $_{\rm d}$ for U=D = 2, $_{\rm L}$ = E_C = 0:1D, and N_B = 0. Dashed line: The localm om ent estim ate of R ef. 5. (b) The charge curve hN i vs N_B, for $_{\rm d}$ =D = 1; 1:581; 1:733; 1:843, and 1:935 (solid, dashed, dotted, dot-dashed, and long-dashed line, respectively). For each value of $_{\rm d}$, $_{\rm B}$ is tuned to the corresponding N_B = 0 value of $_{\rm B}^{2C\,{\rm K}}$, depicted in panel (a).

the charge step dram atically changes upon going from the local-m om ent to the m ixed-valent regime [see Fig.3(b)]. For $_{\rm d}$ = U=2, one recovers a conventional C oulom b-blockade staircase, with charge plateaus at integer units of charge. Upon decreasing $_{\rm d}$, the C oulom b staircase is gradually sm eared, until it is essentially washed out for $_{\rm d}$ =D 1:73. Upon further decreasing $_{\rm d}$, there is a reentrance of the C oulom b staircase. However, the



FIG.4: (a) The capacitance of the box and (b) the magnetic susceptibility of the dot, for U=D = 2, $_L = E_C = 0.1D$, $N_B = 0$, and di erent values of $_d=D$, as specied in the legends. For each $_d$, $_B$ is tuned to the corresponding $N_B = 0$ value of $_B^{2CK}$. Both (T) and C (T) diverge logarithm ically as T ! 0, but with di erent K ondo scales T_K^{SP} and T_K^{ch} , extracted from the slopes of their ln (T) diverging term s. In going from $_d=D = 1.581$ to $_d=D = 1.935$, $k_B T_K^{SP}=D$ takes the values 0.0022;0:0054;0:0457;0:187, and 1:72, while $k_B T_K^{ch}=D$ equals 1:035;0:36;0:035;0:009, and 0:00138, respectively.



FIG. 5: The zero-tem perature conductance of the two-lead device proposed in R ef.5, for U=D = 1, $E_C = D = 0$:1, $N_B = 0$, and di erent values of $_d$. The tunneling rates $_1$ and $_r$ are kept xed in all curves, with $_1 + _r = 0$:1D. Here $G_0h=2e^2$ equals 4 $_1 r=(_1+_r)^2$.

degeneracy points are shifted to integer values of N $_{\rm B}$, and the charge plateaus occur at half-integer units of charge.

To understand this surprising shift of the Coulomb staircase, we note that it happens for $\frac{2C K}{B}$ several times larger than L and E_{C} . We therefore diagonalize rst the local problem of the dot and the two box degrees of freedom directly coupled to it, before incorporating the smaller scales $_{\rm L}$ and ${\rm E}_{\rm C}$. For U tв U + d, the ground state of the local problem is a strong admixture of the dot and box degrees of freedom, whose respective occupancies are 3=2 and 1=2. Switching on E_C, the remaining box degrees of freedom not directly coupled to the dot thus experience an e ective charging-energy interaction similar to that of Eq. (1), but with $N_{\rm B}$ shifted by half an integer. The resulting integer charge plateaus for the remaining box degrees of freedom translate then to half-integer charge plateaus for the entire box.

The most striking feature of particle-hole asymmetry is the entanglem ent of spin and charge within the 2CKE that develops. As demonstrated in Fig. 4 for $N_{\rm B} = 0$ U=2, there is a simultaneand di erent values of $d \in$ ous ln (T) divergence of the dot susceptibility (T) and the box capacitance C (T) = $(e^2 = 2E_C)dh\hat{N} = dN_B$, when $_{\rm B}$ is tuned to the corresponding N $_{\rm B}$ = 0 value of $_{\rm R}^{\rm 2C\,K}$. Hence, the resulting 2CKE is neither of pure spin nor of pure charge character, but rather involves both sectors. Quite rem arkably, the degeneracy point where C (T ! 0)diverges is pinned at N $_{\rm B}$ = 0 for all $_{\rm d}$, although the charge curves of Fig. 3(b) show no particular symmetry about this point. Moreover, there are two distinct K ondo scales, T_{K}^{sp} and T_{K}^{ch} , extracted from the slopes of the $\ln(T)$ diverging terms in (T) and C (T). Upon decreasing d from U=2 to U, T_{k}^{sp} m onotonically increases while T_K^{ch} m onotonically decreases. This marks a continuous transition from a predom inantly spin 2CKE

deep in the local-m om ent regime, to a predom inantly charge 2CKE, rem in iscent of M atveev's scenario, 4,14 in the strongly m ixed-valent regime.

Experimentally, the relevant temperature scale is the crossover temperature T_0 , below which the 2CKE sets in. Estimating T_0 from the NRG level ow, we not that it roughly traces $T_{m\ in}$ = m inf $T_K^{\rm SP}$; $T_K^{\rm ch}g$. The latter scale is greatly enhanced when spin and charge are strongly entangled, reaching a maximum of $k_B\ T_{m\ in}$ 0.4Ec for the model parameters of Fig. 4. Hence, the conditions for observing the 2CKE in realistic quantum -dot devices are most favorable when the spin and charge degrees of freedom are strongly entangled.

The dot susceptibility is very useful theoretically for analyzing the 2CKE, but di cult to measure for a single dot. In Fig. 5 we depict the T = 0 conductance, G (0), for the two-lead device proposed in Ref. 5. Here the single lead is replaced with two separate leads, characterized by the tunneling rates $\ _{1}$ and $\ _{r}.$ In equilibrium , this setting is equivalent⁵ to a single lead with L = 1 + r. At T = 0, the conductance is proportional to the dot spectral function at the Ferm ienergy, which we calculate using the NRG. Fixing $_1$ and $_r$, G (0) drops abruptly as B crosses B . However, in contrast to the treatment of Ref. 6, the height of the conductance step is not xed. It decreases in size with increasing charge uctuations on the dot. Indeed, away from the K ondo lim it G (0) neither vanishes for $_{\rm B}$ > $\frac{2CK}{B}$ nor reaches the unitary limit for $_{\rm B}^{\rm 2C\,K}$. In the m ixed-valent regim e, G (0) actually в < develops a maximum at $_{\rm B} = \frac{2CK}{B} + 0$, re ecting the crossover to a M atveev-type charge 2CKE.

In sum m ary, we found a line of two-channel xed points in a double-dot device, characterized by the number of excess electrons in the box and by the ratio of the tunneling rates. These xed points goven the crossover from one Ferm i liquid to another, and are experimentally detectable by a sharp drop in the conductance. Charge and spin degrees of freedom are generally entangled, and decouple only at special particle-hole sym m etry points such as $N_B = 0$ and $_d = U=2$. The crossover temperature to the two-channelK ondo e ect is greatly enhanced away from the local-m om ent regime, making this exotic e ect accessible in realistic quantum -dot devices.

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